

128K x 36 Bit Synchronous Dual I/O, Dual Address SRAM

The MCM63D736 is a 4M-bit static random access memory, organized as 128K words of 36 bits. It features common data input and data output buffers and incorporates input and output registers on-board with high speed SRAM.

The MCM63D736 allows the user to concurrently perform reads, writes, or pass–through cycles in combination on the two data ports. The two address ports (AX, AY) determine the read or write locations for their respective data ports (DQX, DQY).

The synchronous design allows for precise cycle control with the use of an external single clock (K). All signal pins except output enables $(\overline{GX}, \overline{GY})$ are registered on the rising edge of clock (K).

The pass–through feature allows data to be passed from one port to the other, in either direction. The $\overline{\text{PTX}}$ input must be asserted to pass data from port X to port Y. The $\overline{\text{PTY}}$ will likewise pass data from port Y to port X. A pass–through operation takes precedence over a read operation.

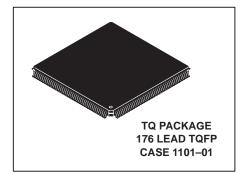
For the case when AX and AY are the same, certain protocols are followed. If both ports are read, the reads occur normally. If one port is written and the other is read, the read from the array will occur before the data is written. If both ports are written, only the data on DQY will be written to the array.

- Single 3.3 V ±5% Power Supply
- 133 MHz Maximum Clock Frequency
- Throughput of 4.8 Gigabits/Second
- Single Clock Operation
- · Self-Timed Write
- Two Bi-Directional Data Buses
- Can be Configured as Separate I/O
- Pass–Through Feature
- Asynchronous Output Enables (GX, GY)
- LVTTL Compatible I/O
- Concurrent Reads and Writes
- 176-Pin TQFP Package

Suggested Applications

- ATM
 Ethernet Switches
 Routers
 Cellular Base Stations
 SNA Switches
 Shared Memory
 RAID Systems
- Cell/Frame bullets SNA Switches Shared Memory RAID Systems

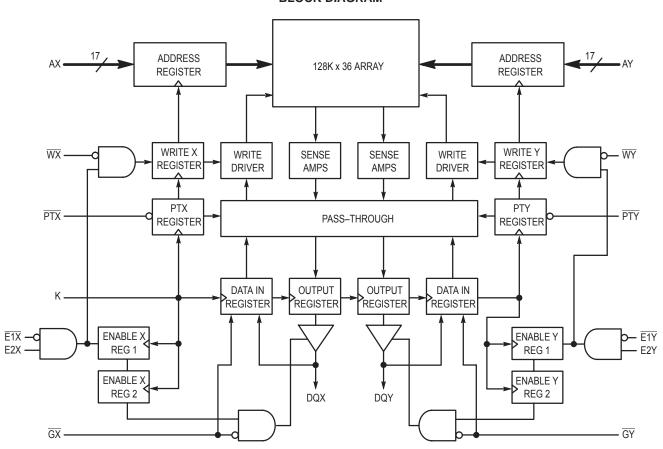
MCM63D736



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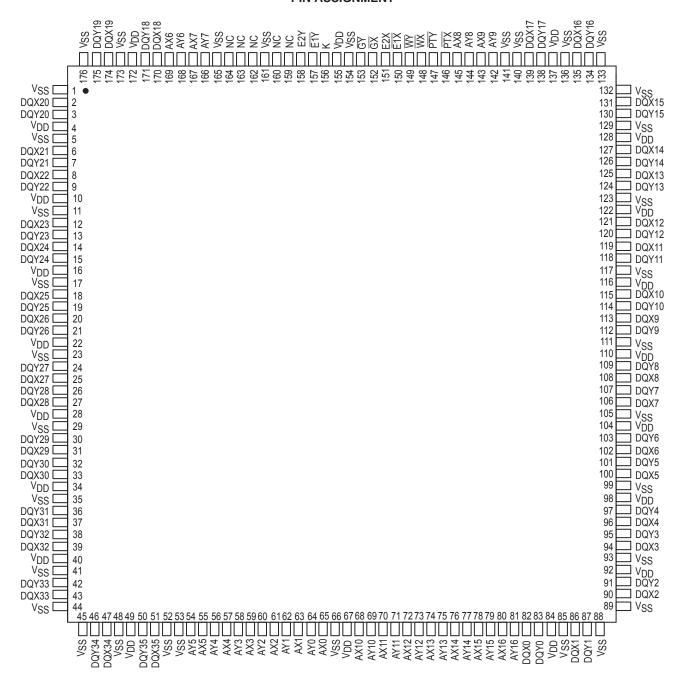


BLOCK DIAGRAM





PIN ASSIGNMENT





PIN DESCRIPTIONS

Pin Locations	Symbol	Type	Description
65, 63, 61, 59, 57, 55, 169, 167, 145, 143, 68, 70, 72, 74, 76, 78, 80	AX0 – AX16	Input	Address Port X: Never allow floating addresses for inputs AX0 – AX16 A pullup resistor is needed.
64, 62, 60, 58, 56, 54, 168, 166, 144, 142, 69, 71, 73, 75, 77, 79, 81	AY0 – AY16	Input	Address Port Y: Never allow floating addresses for inputs AY0 – AY16. A pullup resistor is needed.
82, 86, 90, 94, 96, 100, 102, 106, 108, 113. 115, 119, 121, 125, 127, 131, 135, 139, 170, 174, 2, 6, 8, 12, 14, 18, 20, 25, 27, 31, 33, 37, 39, 43, 47, 51	DQX0 – DQX35	I/O	Data Input/Output Port X.
83, 87, 91, 95, 97, 101, 103, 107, 109, 112, 114, 118, 120, 124, 126, 130, 134, 138, 171, 175, 3, 7, 9, 13, 15, 19, 21, 24, 26, 30, 32, 36, 38, 42, 46, 50	DQY0 – DQY35	I/O	Data Input/Output Port Y.
150	E1X	Input	Synchronous Chip Enable Port X: Active low.
151	E2X	Input	Synchronous Chip Enable Port X: Active high.
157	E1Y	Input	Synchronous Chip Enable Port Y: Active low.
158	E2Y	Input	Synchronous Chip Enable Port Y: Active high.
152	GΧ	Input	Asynchronous Output Enable Port X Input: Low — enables output buffers (DQXx pins). High — DQXx pins are high impedance.
153	GY	Input	Asynchronous Output Enable Port Y Input: Low — enables output buffers (DQYx pins). High — DQYx pins are high impedance.
156	К	Input	Clock: This signal registers the address, data in, and all control signals except $\overline{\mathbf{G}}.$
146	PTX	Input	Pass–Through Port X.
147	PTY	Input	Pass–Through Port Y.
148	WX	Input	Synchronous Write Enable Port X.
149	WY	Input	Synchronous Write Enable Port Y.
4, 10, 16, 22, 28, 34, 40, 49, 67, 84, 92, 98, 104, 110, 116, 122, 128, 137, 155, 172	V _{DD}	Supply	3.3 V Power Supply.
1, 5, 11, 17, 23, 29, 35, 41, 44, 45, 48, 52, 53, 66, 85, 88, 89, 93, 99, 105, 111, 117, 123, 129, 132, 133, 136, 140, 141, 154, 161, 165, 173, 176	V _{SS}	Supply	Ground.
159, 159, 160, 162, 163, 164	NC	_	No Connection: There is no connection to the chip.

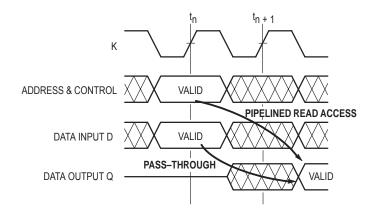


TRUTH TABLE (See Notes 1 through 6)

Operation	Input at t _n Clock										
No.					E1Y	E2Y	WX	WY	PTX	PTY	Operation
1	Н	Х	Н	Х	Х	Х	Х	Х	Deselected		
2	Х	L	Х	L	Х	Х	Х	Х	Deselected		
3	L	Н	Х	Х	L	Х	Х	Х	Write X Port		
4	Х	Х	L	Н	Х	L	Х	Х	Write Y Port		
5	L	Н	L	Н	Х	Х	L	Х	Pass–Through X to Y		
6	L	Н	L	Н	Х	Х	Х	L	Pass–Through Y to X		
7	L	Н	Х	Х	Н	Х	Н	Н	Read X		
8	Х	Х	L	Н	Х	Н	Н	Н	Read Y		

NOTES:

- 1. L = Logic Low; H = Logic High; X = Don't Care.
- 2. GX/GY must be negated during write and pass-through cycles.
- 3. Operation numbers 3 6 can be used in any combination.
- 4. Operation numbers 4 and 7, 3 and 8, 7 and 8 can be combined.
- 5. Operation number 5 can not be combined with operation number 7 or 8 because pass-through takes precedence over a read operation.
- 6. Operation number 6 can not be combined with operation number 7 or 8 because pass-through takes precedence over a read operation.



ABSOLUTE MAXIMUM RATINGS (See Notes)

Rating	Symbol	Value	Unit
Power Supply Voltage	V_{DD}	-0.5 to 4.6	V
Voltage Relative to V _{SS} for Any Pin Except V _{DD}	V _{in} , V _{out}	–0.5 to V _{DD} + 0.5	V
Output Current	l _{out}	±20	mA
Package Power Dissipation	PD	1.6	W
Temperature Under Bias	T _{bias}	-10 to 85	°C
Storage Temperature — Plastic	T _{stg}	-55 to 125	°C

NOTES

- Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to RECOMMENDED OPERATING CONDITIONS. Exposure to higher than recommended voltages for extended periods of time could affect device reliability.
- Power dissipation capability is dependent upon package characteristics and use environment. See Package Thermal Characteristics.

This is a synchronous device. All synchronous inputs must meet specified setup and hold times with stable logic levels for *ALL* rising edges of clock (K) while the device is selected.

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to these high—impedance circuits.



PACKAGE THERMAL CHARACTERISTICS (See Note 1)

Rating		Symbol	TQFP	Unit	Notes
Junction to Ambient (@ 200 lfm)	Single–Layer Board Four–Layer Board	$R_{ heta JA}$	35 30	°C/W	2
Junction to Board (Bottom)		$R_{\theta JB}$	23	°C/W	3
Junction to Case (Top)		$R_{\theta JC}$	9	°C/W	4

NOTES:

- 1. Junction temperature is a function of on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, board population, and board thermal resistance.
- 2. Per SEMI G38-87.
- 3. Indicates the average thermal resistance between the die and the printed circuit board.
- 4. Indicates the average thermal resistance between the die and the case top surface via the cold plate method (MIL SPEC-883 Method 1012.1).

DC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{DD} = 3.3 \text{ V} \pm 5\%, T_{A} = 0^{\circ} \text{ to } 70^{\circ}\text{C}, \text{ Unless Otherwise Noted})$

RECOMMENDED OPERATING CONDITIONS AND SUPPLY CURRENTS

Parameter	Symbol	Min	Max	Unit
Supply Voltage (Operating Voltage Range)	V _{DD}	3.135	3.465	V
Input High Voltage	VIH	2.0	V _{DD} + 0.5**	V
Input Low Voltage	V _{IL}	-0.5*	0.8	V
Input Leakage Current (All Inputs, V _{in} = 0 to V _{DD})	llkg(l)	_	±1.0	μΑ
Output Leakage Current ($\overline{E} = V_{IH}$, $V_{out} = 0$ to V_{DD})	l _{lkg(O)}	_	±1.0	μΑ
AC Supply Current (I _{out} = 0 mA) (V _{DD} = Max, f = f _{max})	I _{DDA} -133 I _{DDA} -100 I _{DDA} -83	_	400 350 325	mA
CMOS Standby Supply Current (Deselected, Clock (K) Cycle Time \geq t _{KHKH} , All Inputs Toggling at CMOS Levels $V_{in} \leq V_{SS} + 0.2 \text{ V or } \geq V_{DD} - 0.2 \text{ V})$	^I SB1	_	100	mA
Output Low Voltage (I _{OL} = 8.0 mA)	V _{OL}	_	0.4	V
Output High Voltage (I _{OH} = -4.0 mA)	Voн	2.4	V_{DD}	V

^{*} $V_{IL} \ge -1.5 \text{ V for } t \le t_{KHKH}/2.$

CAPACITANCE (f = 1.0 MHz, T_A = 0° to 70°C, Periodically Sampled Rather Than 100% Tested)

Parameter	Symbol	Max	Unit
Address and Data Input Capacitance	C _{in}	6	pF
Control Pin Input Capacitance	C _{in}	6	pF
Output Capacitance	C _{out}	8	pF

^{**} $V_{IH} \le V_{DD} + 1.0 \text{ V}$ (not to exceed 4.6 V) for $t \le t_{KHKH}/2$.



AC OPERATING CONDITIONS AND CHARACTERISTICS

 $(V_{DD} = 3.3 \text{ V} \pm 5\%, T_{A} = 0^{\circ} \text{ to } 70^{\circ}\text{C}, \text{ Unless Otherwise Noted})$

Input Timing Measurement Reference Level 1.5 V	Output Timing Reference Level 1.5 V
Input Pulse Levels 0 to 3.0 V	Output Load Figure 1 Unless Otherwise Noted
Input Rise/Fall Time	

READ/WRITE CYCLE TIMING (See Notes 1, 2, and 3)

		MCM63E	0736–133	MCM63D	736–100	MCM63I	D736–83		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Notes
Cycle Time	tkhkh	7.5	_	10	_	12	_	ns	1
Clock Access Time	t _{KHQV}	<u> </u>	4	_	5	_	6	ns	
Clock Low Pulse Width	tKLKH	3	_	4	_	4	_	ns	
Clock High Pulse Width	tKHKL	3	_	4	_	4	_	ns	
Clock High to Data Output Active	tKHQX1	0	_	0	_	0	_	ns	
Clock High to Data Output Invalid	tKHQX2	1	_	1	_	1	_	ns	
Clock High to Data Output High–Z	t _{KHQZ}	T -	3	_	3	_	4	ns	2
Output Enable Low to Data Output Valid	^t GLQV	_	4	_	5	_	6	ns	
Output Enable Low to Data Output Low-Z	^t GLQX	0	_	0	_	0	_	ns	
Output Enable High to Data Output High–Z	^t GHQZ	_	3	_	3	_	5	ns	2
Setup Times: AWR0 – AWR10 ARD0 – ARD10 V E1X, E2X, E1Y, E2Y D0 – D3	tAVKH tWVKH tPTVKH tEVKH	1.5	_	1.5	_	2.5	_	ns	3
Hold Times: AWR0 – AWR10 ARD0 – ARD10 V P ⁻ E1X, E2X, E1Y, E2Y D0 – D38	tKHAX tKHWX tKHPTX tKHEX	0.5	_	0.5	_	0.5	_	ns	3

NOTES:

- 1. All read and write cycles are referenced from K.
- 2. This parameter is sampled and not 100% tested.
- 3. This is a synchronous device. All synchronous inputs must meet the specified setup and hold times with stable logic levels for *ALL* rising edges of clock (K) while the device is selected.

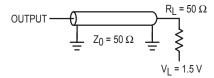
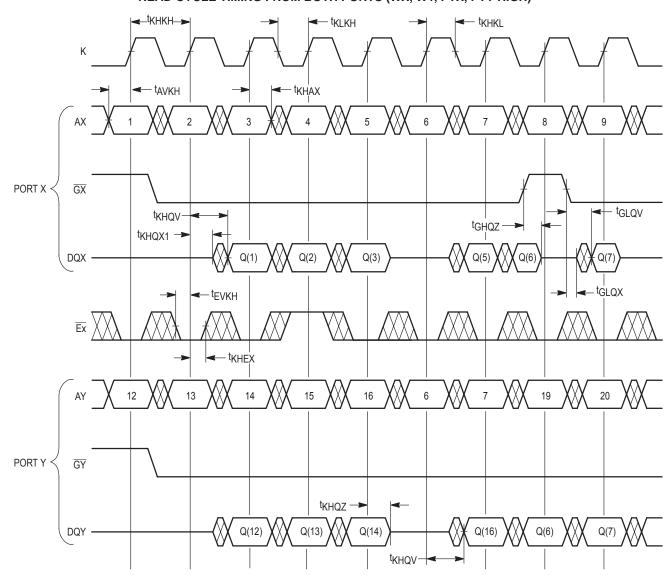


Figure 1. AC Test Load



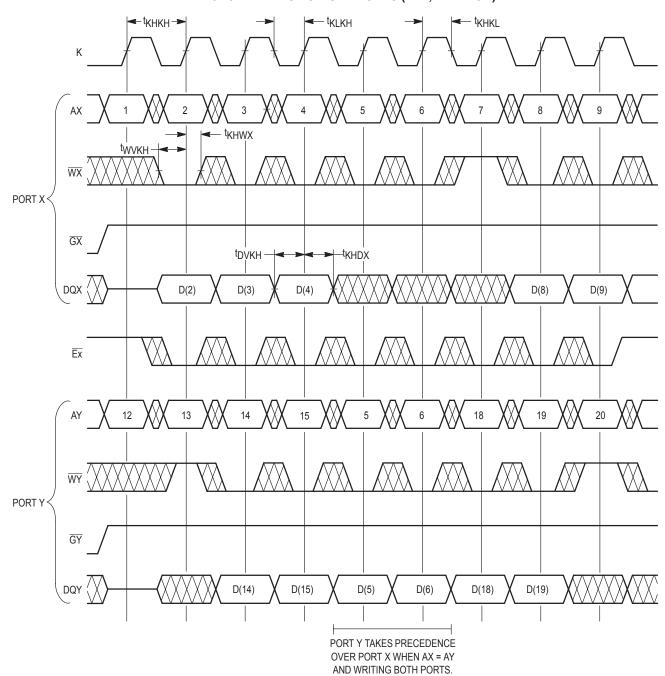
READ CYCLE TIMING FROM BOTH PORTS (WX, WY, PTX, PTY HIGH)



NOTE: \overline{Ex} Low = $\overline{E1x}$ Low and E2x High. \overline{Ex} High = $\overline{E1x}$ High or E2x Low.



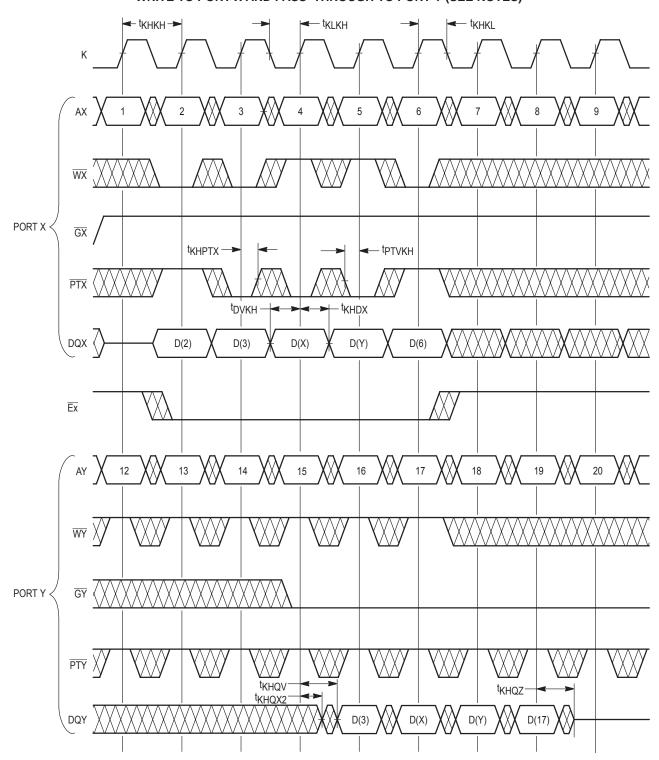
WRITE CYCLE TIMING TO BOTH PORTS (PTX, PTY HIGH)



NOTE: \overline{Ex} Low = $\overline{E1x}$ Low and $\overline{E2x}$ High. \overline{Ex} High = $\overline{E1x}$ High or $\overline{E2x}$ Low.



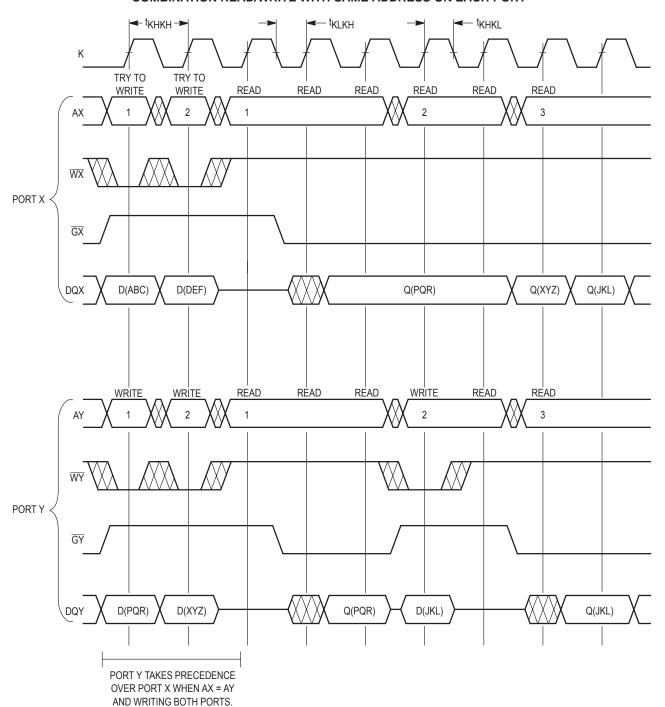
WRITE TO PORT X AND PASS-THROUGH TO PORT Y (SEE NOTES)



NOTES: $\overline{\text{Ex}}$ Low = $\overline{\text{E1x}}$ Low and E2x High. $\overline{\text{Ex}}$ High = $\overline{\text{E1x}}$ High or E2x Low. The timing diagram is valid for the opposite case as well, i.e., writing to Port Y and passing through to Port X.



COMBINATION READ/WRITE WITH SAME ADDRESS ON EACH PORT



NOTES: $\overline{PTX} = \overline{PTY} = \text{high}$.

D(Value) = Value is the input to the data port. Q(Value) = Value is the output from the data port.



ORDERING INFORMATION (Order by Full Part Number)

Freescale Memory Prefix

Part Number

Speed (133 = 133 MHz, 100 = 100 MHz, 83 = 83 MHz)

Package (TQ = TQFP)

MCM63D736TQ100

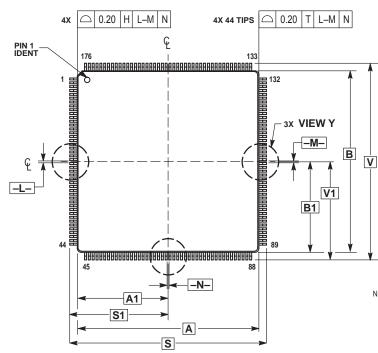
MCM63D736TQ83

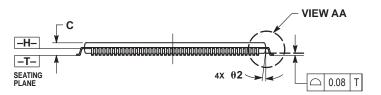
Full Part Numbers — MCM63D736TQ133

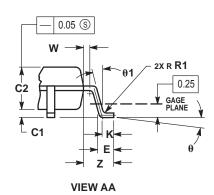


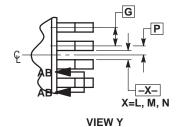
PACKAGE DIMENSIONS

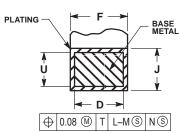
TQFP PACKAGE 176-LEAD CASE 1101-01











SECTION AB-AB ROTATED 90° CLOCKWISE

NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DATUM PLANE -H- IS LOCATED AT BOTTOM OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE THE LEAD EXITS THE PLASTIC BODY AT THE BOTTOM OF THE PARTING LINE.
- 4. DATUMS -L-, -M-, AND -N- TO BE DETERMINED AT DATUM PLANE -H-
- DIMENSIONS S AND V TO BE DETERMINED AT SEATING PLANE -T-. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS 0.25 (0.010) PER SIDE. DIMENSIONS A AND B DO INLCUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. DAMBAR PROTRUSION SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.35 (0.014) MINIMUM SPACE BETWEEN PROTRUSION AND ADJACENT LEAD $0.07\ (0.003)$.

	MILLIMETERS							
DIM	MIN	MAX						
Α	24.00 BSC							
A1	12.00	BSC						
В	24.00	BSC						
B1	12.00	BSC						
С		1.60						
C1	0.05							
C2	1.35	1.45						
D	0.17	0.23						
Е	0.45	0.75						
F	0.17	0.27						
G	0.50	BSC						
J	0.09	0.20						
K	0.50	0.50 REF						
Р	0.25	BSC						
R1	0.10	0.20						
S	26.00	BSC						
S1	13.00	BSC						
U	0.09	0.16						
٧	26.00	BSC						
V1	13.00	13.00 BSC						
W	0.20 REF							
Z	1,00	REF						
θ	0 °	7°						
θ1	0 °							
θ2	12 °REF							





NOTES



NOTES



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